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# **General Purpose Transistors**

**PNP Silicon** 

# MMBT2907AL, SMMBT2907AL

#### Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	-60	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	-60	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	Vdc
Collector Current – Continuous	Ι <sub>C</sub>	-600	mAdc
Collector Current – Peak (Note 3)	I <sub>CM</sub>	-1200	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation – FR–5 Board (Note 1) @T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation – Alumina Substrate, (Note 2) @T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	m₩ m₩/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Total Device Dissipation – Heat Spreader or equivalent, (Note 4) @T <sub>A</sub> = 25°C	P <sub>D</sub>	350	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	357	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

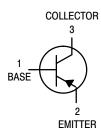
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.

2. Alumina = 0.4  $\times$  0.3  $\times$  0.024 in. 99.5% alumina.

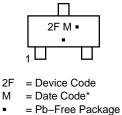
3. Reference SOA curve.

4. Heat Spreader or equivalent = 450 mm<sup>2</sup>, 2 oz.





#### MARKING DIAGRAM



(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MMBT2907ALT1G	SOT-23	3000 / Tape &
SMMBT2907ALT1G	(Pb-Free)	Reel
MMBT2907ALT3G	SOT-23	10,000 / Tape &
SMMBT2907ALT3G	(Pb-Free)	Reel

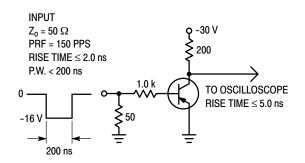
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

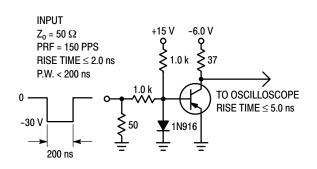
Characteristic			Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (Nor ( $I_C = -1.0 \text{ mAdc}, I_B = 0$ ) ( $I_C = -10 \text{ mAdc}, I_B = 0$ )	te 5)	V <sub>(BR)CEO</sub>	-60 -60		Vdc
Collector-Base Breakdown Voltage (I <sub>C</sub> =	= -10 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	-60	-	Vdc
Emitter-Base Breakdown Voltage (I <sub>E</sub> = -	-10 μAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	-5.0	-	Vdc
Collector Cutoff Current ( $V_{CE} = -30$ Vdc,	V <sub>EB(off)</sub> = -0.5 Vdc)	ICEX	-	-50	nAdc
		I <sub>CBO</sub>		-0.010 -10	μAdc
Base Cutoff Current (V <sub>CE</sub> = $-30$ Vdc, V <sub>EE</sub>	$B_{\rm (off)} = -0.5 \ \rm Vdc)$	I <sub>BL</sub>	-	-50	nAdc
ON CHARACTERISTICS					
$ \begin{array}{l} \text{DC Current Gain} \\ (I_{C}=-0.1 \text{ mAdc}, V_{CE}=-10 \text{ Vdc}) \\ (I_{C}=-1.0 \text{ mAdc}, V_{CE}=-10 \text{ Vdc}) \\ (I_{C}=-10 \text{ mAdc}, V_{CE}=-10 \text{ Vdc}) \\ (I_{C}=-150 \text{ mAdc}, V_{CE}=-10 \text{ Vdc}) \\ (I_{C}=-500 \text{ mAdc}, V_{CE}=-10 \text{ Vdc}) \\ (I_{C}=-500 \text{ mAdc}, V_{CE}=-10 \text{ Vdc}) \end{array} $	ie 5)	h <sub>FE</sub>	75 100 100 100 50	- - 300 -	_
Collector – Emitter Saturation Voltage (Not ( $I_C = -150$ mAdc, $I_B = -15$ mAdc) (Not ( $I_C = -500$ mAdc, $I_B = -50$ mAdc)		V <sub>CE(sat)</sub>		-0.4 -1.6	Vdc
Base – Emitter Saturation Voltage (Note 5 ( $I_C = -150$ mAdc, $I_B = -15$ mAdc) ( $I_C = -500$ mAdc, $I_B = -50$ mAdc)	5)	V <sub>BE(sat)</sub>		-1.3 -2.6	Vdc
SMALL-SIGNAL CHARACTERISTICS			-	-	-
Current-Gain – Bandwidth Product (Notes 5, 6), ( $I_C = -50$ mAdc, $V_{CE} = -20$ Vdc, f = 100 MHz)		f <sub>T</sub>	200	-	MHz
Output Capacitance ( $V_{CB} = -10$ Vdc, $I_E = 0$ , f = 1.0 MHz)		C <sub>obo</sub>	-	8.0	pF
Input Capacitance ( $V_{EB} = -2.0 \text{ Vdc}$ , $I_C = 0$ , f = 1.0 MHz)		C <sub>ibo</sub>	-	30	
SWITCHING CHARACTERISTICS					
Turn–On Time		t <sub>on</sub>	-	45	
Delay Time	$(V_{CC} = -30 \text{ Vdc}, I_C = -150 \text{ mAdc}, I_{B1} = -15 \text{ mAdc})$	t <sub>d</sub>	-	10	
Rise Time		t <sub>r</sub>	-	40	
Turn–Off Time		t <sub>off</sub>	-	100	ns
Storage Time	$(V_{CC} = -6.0 \text{ Vdc}, I_C = -150 \text{ mAdc}, I_{B1} = I_{B2} = -15 \text{ mAdc})$	t <sub>s</sub>	-	80	]
Fall Time		t <sub>f</sub>	-	30	]

5. Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  2.0%.

6.  $f_T$  is defined as the frequency at which  $|h_{fe}|$  extrapolates to unity.

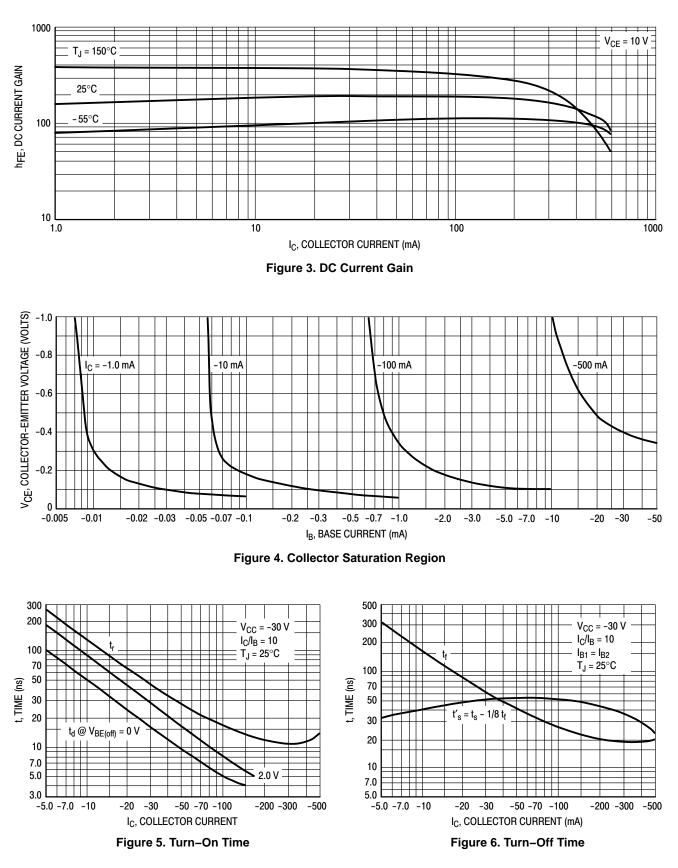






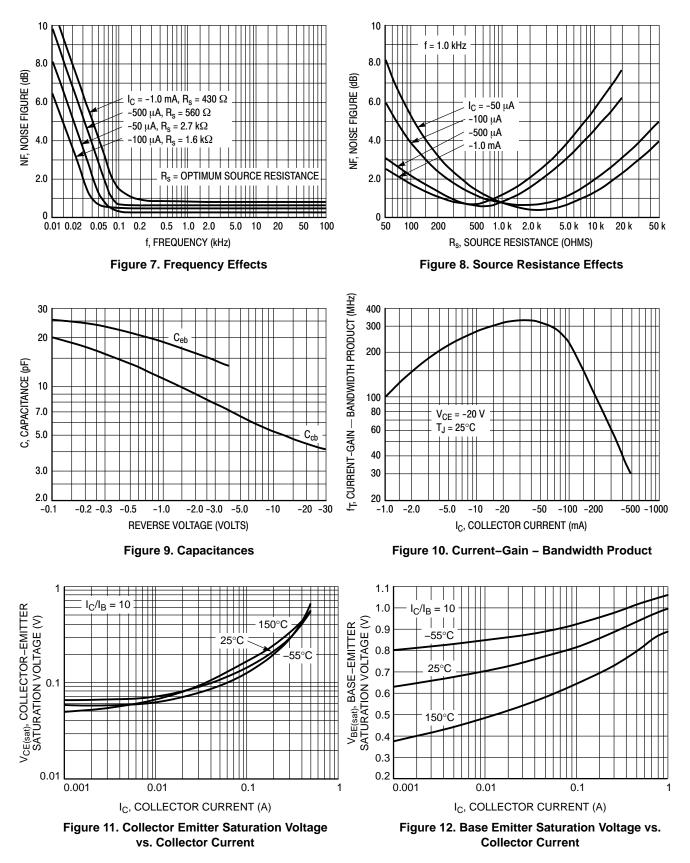
#### Figure 2. Storage and Fall Time Test Circuit

**TYPICAL CHARACTERISTICS** 





 $V_{CE}$  = 10 VDC,  $T_A$  = 25°C





 $V_{CE}$  = 10 VDC,  $T_A$  = 25°C

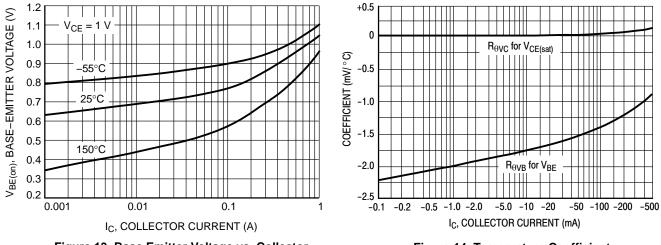




Figure 14. Temperature Coefficients

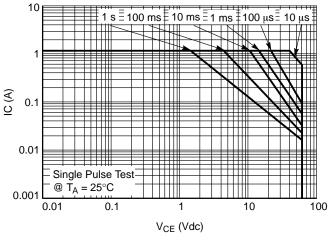


Figure 15. Safe Operating Area

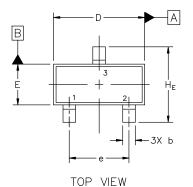
# semi

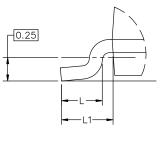


#### SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318**

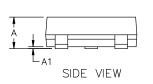
**ISSUE AU** 

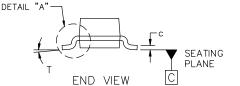
DATE 14 AUG 2024









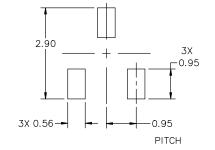




XXX = Specific Device Code М = Date Code

= Pb-Free Package .

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



MILLIMETERS					
DIM	MIN	NOM	МАХ		
А	0.89	1.00	1.11		
A1	0.01	0.06	0.10		
b	0.37	0.44	0.50		
с	0.08	0.14	0.20		
D	2.80	2.90	3.04		
E	1.20	1.30	1.40		
е	1.78	1.90	2.04		
L	0.30	0.43	0.55		
L1	0.35	0.54	0.69		
Ηe	2.10	2.40	2.64		
Т	0°		10°		

NOTES:

DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS: 1.

2. MILLIMETERS.

MILLIME IERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE 3.

BASE MATERIAL. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, 4. PROTRUSIONS, OR GATE BURRS.

#### RECOMMENDED MOUNTING FOOTPRINT

\* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## **STYLES ON PAGE 2**

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DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	I	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	I PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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